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# FQP6N40CF

# N-Channel QFET<sup>®</sup> FRFET<sup>®</sup> MOSFET 400 V, 6 A, 1.1 $\Omega$

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

## Features

- 6 A, 400 V,  $R_{DS(on)}$  = 1.1  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 3 A
- Low Gate Charge (Typ. 16 nC)
- Low C<sub>rss</sub> (Typ. 15 pF)
- 100% Avalanche Tested



## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter			FQP6N40CF	Unit
V <sub>DSS</sub>	Drain-Source Volt	age		400	V A
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		6	
		- Continuous (T <sub>C</sub> = 100°C)		3.6	Α
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	24	Α
V <sub>GSS</sub>	Gate-Source Voltage			± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	270	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	6	А
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	73	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20	V/ns
PD	Power Dissipation	(T <sub>C</sub> = 25°C)		73	W
		- Derate above 25°C		0.58	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.			300	°C

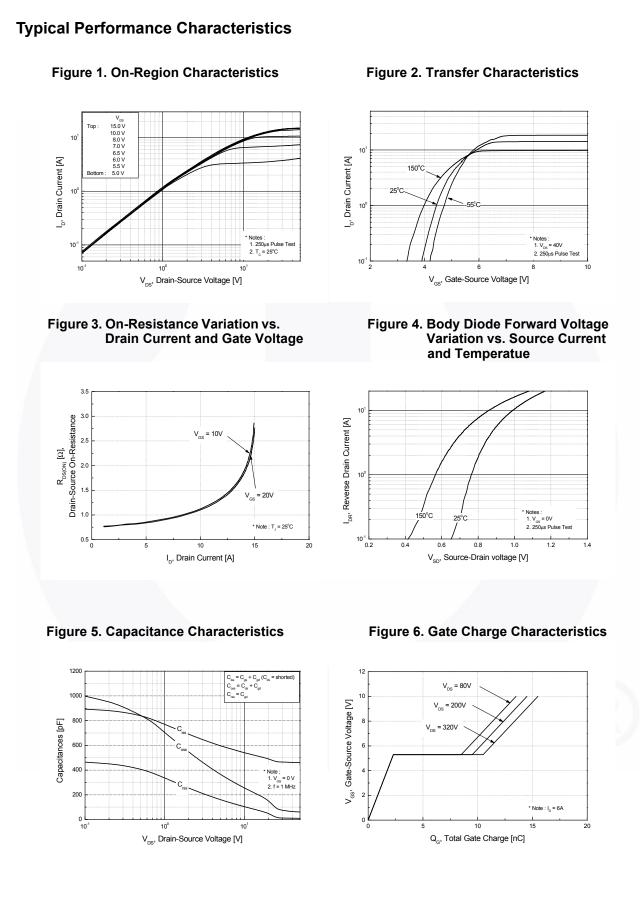
## **Thermal Characteristics**

Symbol	Parameter	FQP6N40CF	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	1.71	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	C/ W

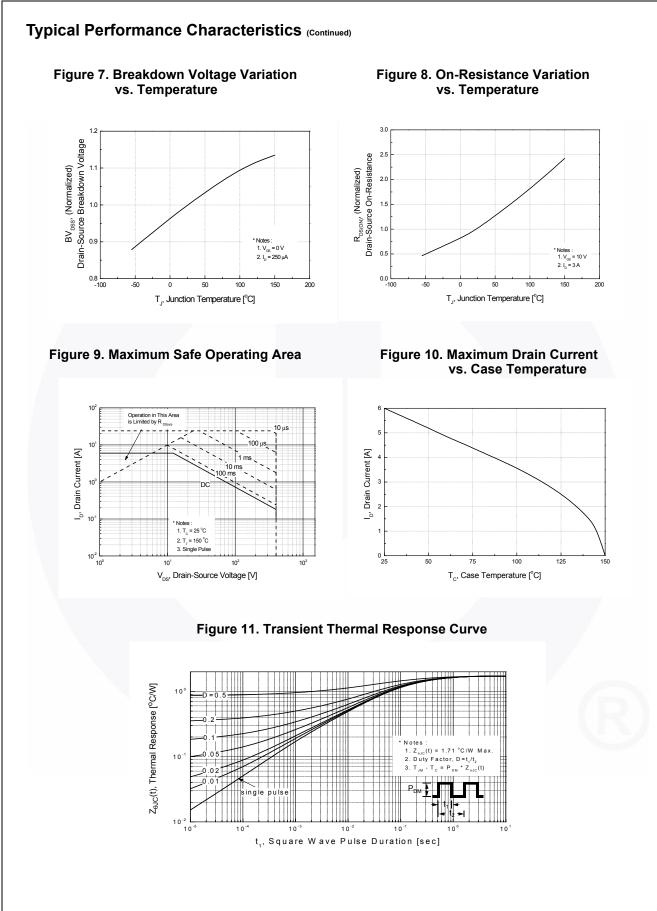
December 2013

FQP6N40	Part Number Top Mark Packa		Package	e Packing Method Reel Siz		ze	Tape Wig	lth	Quantity	
			TO-220	Tube	N/A		N/A		50 units	
Electrica	al Cha	aracteristics T	c = 25°C un	less otherwise noted.						
Symbol Parameter			Test Conditions		Min.	Тур.	Max.	Unit		
Off Characte	eristics		l		Ļ		1			
BV <sub>DSS</sub>	Drain	-Source Breakdown Vol	tage	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A		400			V	
ΔΒV <sub>DSS</sub> /ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient			$I_D$ = 250 µA, Referenced to 25°C			0.54		V/°C	
I <sub>DSS</sub>	Zero	Gate Voltage Drain Curr	ent	$V_{DS}$ = 400 V, $V_{GS}$ = 0 V				1	μA	
				$V_{DS}$ = 320 V, $T_{C}$ = 125°C				10	μA	
I <sub>GSSF</sub>	Gate	Gate-Body Leakage Current, Forward		$V_{GS}$ = 30 V, $V_{DS}$ = 0 V				100	nA	
I <sub>GSSR</sub>	Gate	-Body Leakage Current,	Reverse	$V_{GS}$ = -30 V, $V_{DS}$ = 0 V				-100	nA	
On Characte	eristics									
V <sub>GS(th)</sub>	Gate	Threshold Voltage		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0		4.0	V	
R <sub>DS(on)</sub>	Statio	Static Drain-Source On-Resistance		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$			0.9	1.1	Ω	
9 <sub>FS</sub>	Forw	ard Transconductance		V <sub>DS</sub> = 40 V, I <sub>D</sub> = 3 A			4.7		S	
Dynamic Ch	aracteri	stics								
C <sub>iss</sub>	-	put Capacitance utput Capacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		480	625	pF		
C <sub>oss</sub>	· ·						80	105	pF	
C <sub>rss</sub>	Reve	rse Transfer Capacitanc	e				15	20	pF	
Switching C	haracte	ristics								
		On Delay Time		V <sub>DD</sub> = 200 V, I <sub>D</sub> = 6 A,			13	35	ns	
t <sub>d(on)</sub>	Turn-			$V_{DD}$ = 200 V, $I_D$ = 6 A, R <sub>G</sub> = 25 $\Omega$			13 65	35 140	ns	
t <sub>d(on)</sub>	Turn- Turn-	On Delay Time					-			
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub>	Turn- Turn- Turn-	On Delay Time On Rise Time			(Note 4)		65	140	ns	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn- Turn- Turn- Turn-	On Delay Time On Rise Time Off Delay Time		R <sub>G</sub> = 25 Ω	(Note 4)		65 21	140 55	ns	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub>	Turn- Turn- Turn- Turn- Turn- Total	On Delay Time On Rise Time Off Delay Time Off Fall Time			(Note 4)		65 21 38	140 55 85	ns ns ns	
Switching C           td(on)           tr           td(off)           tf           Qg           Qgs           Qad	Turn- Turn- Turn- Turn- Total Gate	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge		$R_{G} = 25 \Omega$ V <sub>DS</sub> = 320 V, I <sub>D</sub> = 6 A,		  	65 21 38 16	140 55 85	ns ns ns nC	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Turn- Turn- Turn- Turn- Total Gate Gate	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge		$R_{G}^{-} = 25 \Omega$ $V_{DS} = 320 V, I_{D} = 6 A,$ $V_{GS} = 10 V$	(Note 4) (Note 4)		65 21 38 16 2.3	140 55 85 20 	ns ns ns nC nC	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-Sourc	Turn- Turn- Turn- Turn- Total Gate Gate	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge Characteristics and M		$R_{G}^{2}$ = 25 Ω $V_{DS}$ = 320 V, $I_{D}$ = 6 A, $V_{GS}$ = 10 V ings			65 21 38 16 2.3	140 55 85 20  	ns ns nC nC nC	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-Sourc</b> I <sub>S</sub>	Turn- Turn- Turn- Total Gate Gate <b>e Diode</b>	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge <b>Characteristics and M</b> mum Continuous Drain-	Source Diode	$R_G = 25 \Omega$ $V_{DS} = 320 V, I_D = 6 A,$ $V_{GS} = 10 V$ ings Forward Current			65 21 38 16 2.3 8.2	140 55 85 20  	ns ns nC nC nC A	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-Sourc</b> I <sub>S</sub> I <sub>SM</sub>	Turn- Turn- Turn- Total Gate Gate <b>e Diode</b> Maxii	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge Characteristics and M mum Continuous Drain- mum Pulsed Drain-Sour	Source Diode ce Diode For	$R_G = 25 \Omega$ $V_{DS} = 320 V, I_D = 6 A,$ $V_{GS} = 10 V$ ings Forward Current ward Current			65 21 38 16 2.3 8.2	140 55 85 20   6 24	ns ns nC nC nC C A A	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-Sourc</b> I <sub>S</sub> I <sub>SM</sub> V <sub>SD</sub>	Turn- Turn- Turn- Total Gate Gate <b>B</b> Diode Maxin Maxin Drair	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge <b>Characteristics and M</b> mum Continuous Drain- mum Pulsed Drain-Sour -Source Diode Forward	Source Diode ce Diode For	$R_{G}^{2} = 25 \Omega$ $V_{DS} = 320 V, I_{D} = 6 A,$ $V_{GS} = 10 V$ ings Forward Current ward Current $V_{GS} = 0 V, I_{S} = 6 A$		       	65 21 38 16 2.3 8.2   	140 55 85 20  	ns ns nC nC nC nC A A A V	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> <b>Drain-Sourc</b> I <sub>S</sub> I <sub>SM</sub>	Turn- Turn- Turn- Total Gate Gate <b>e Diode</b> Maxin Maxin Drair Reve	On Delay Time On Rise Time Off Delay Time Off Fall Time Gate Charge -Source Charge -Drain Charge Characteristics and M mum Continuous Drain- mum Pulsed Drain-Sour	Source Diode ce Diode For	$R_G = 25 \Omega$ $V_{DS} = 320 V, I_D = 6 A,$ $V_{GS} = 10 V$ ings Forward Current ward Current			65 21 38 16 2.3 8.2	140 55 85 20   6 24	ns ns nC nC nC C A A	

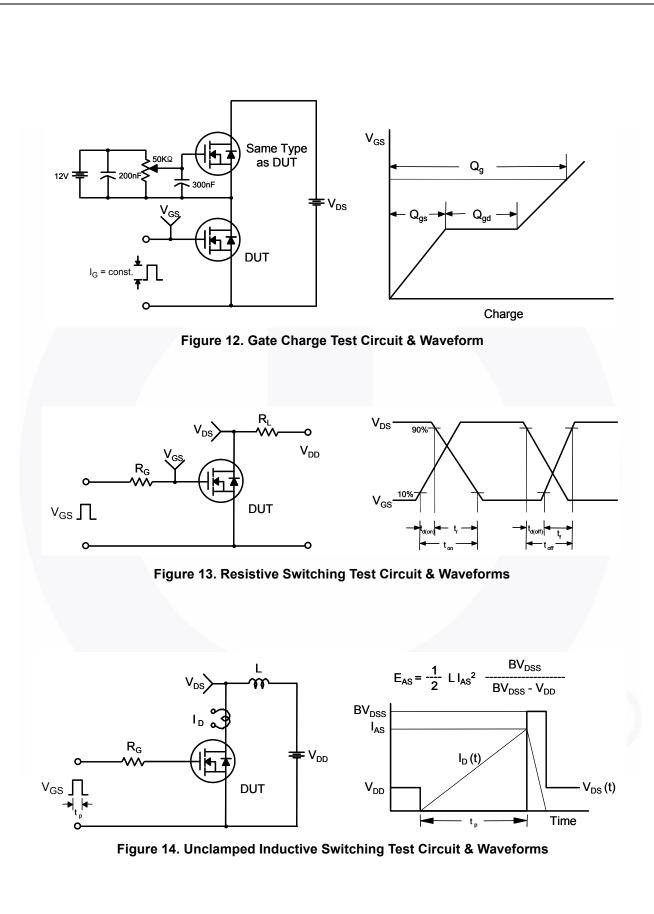




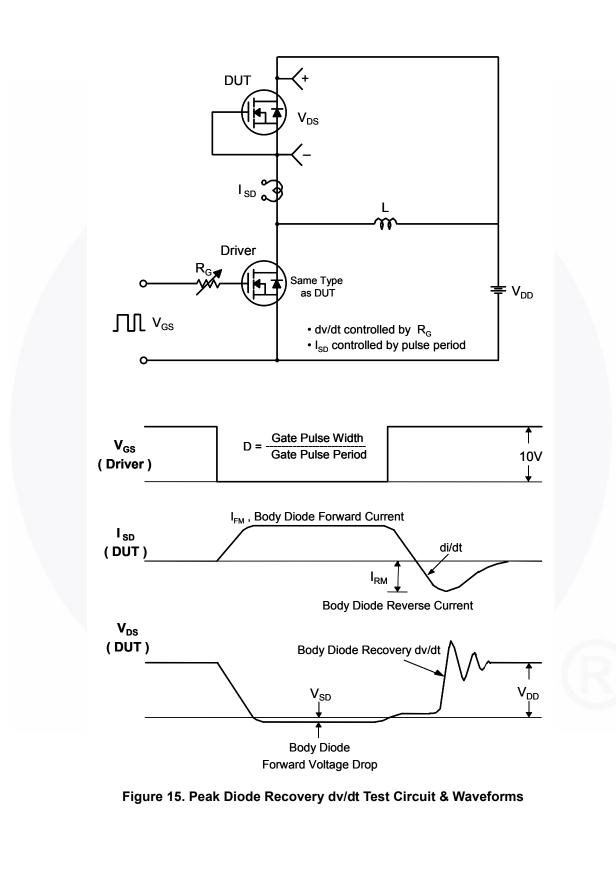
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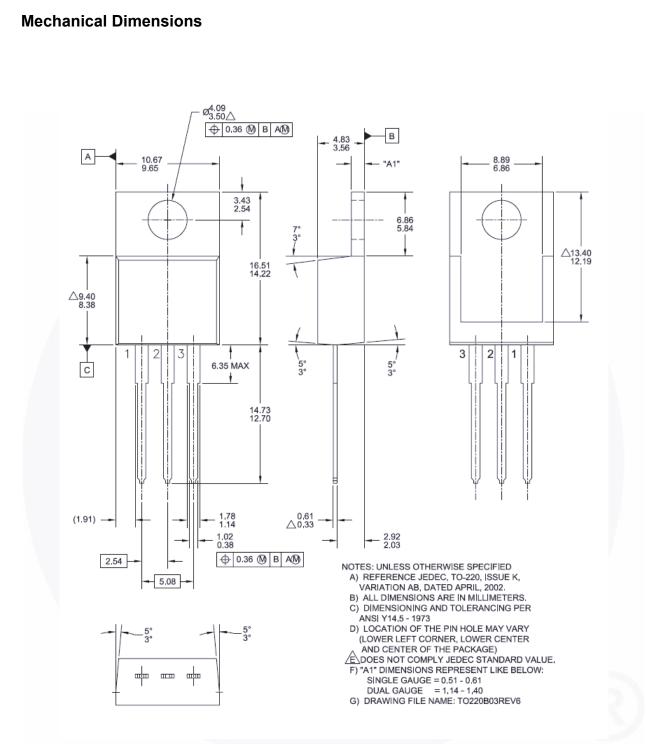


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FQP6N40CF — N-Channel QFET<sup>®</sup> FRFET<sup>®</sup> MOSFET





### Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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